## SD1050

## RF \& MICROWAVE TRANSISTORS VHF-UHF APPLICATIONS

## Features

- 130-400 MHz
- 28 VOLTS
- $\mathrm{P}_{\text {OUt }}=$ 3.0 WATTS
- $\mathrm{G}_{\mathrm{P}}=4.8 \mathrm{~dB}$ MINIMUM
- HIGH POWER GAIN
- COMMON EMITTER CONFIGURATION


## DESERIPTION:

This line of silicon epitaxial NPN planar high frequency transistor employs a multi emitter electrode design. This feature together with a heavily diffused base matrix located between the individual emitters results in high RF current handling capability, high power gain, low base resistance and low output capacitance. These transistors are intended for Class A, B, or C amplifier, oscillator or frequency multiplier circuits and are specifically designed for operation in the VHF-UHF region.


## ABSOLUTE MAXIMUM RATINGS [TCASE $=25^{\circ} \mathrm{C}$ ]

| Symbol | Parameter | Value | Unit |
| :---: | :--- | :---: | :---: |
| $\mathrm{V}_{\mathrm{CBO}}$ | Collector-Base Voltage | $\mathbf{6 5}$ | V |
| $\mathrm{V}_{\mathrm{CES}}$ | Collector-Emitter Voltage | 40 | V |
| $\mathrm{~V}_{\text {EBO }}$ | Emitter-Base VoItage | 4.0 | V |
| $\mathrm{I}_{\mathrm{C}}$ | Device Current | 1.5 | A |
| $\mathrm{P}_{\text {DISS }}$ | Power Dissipation | 11.6 | $\mathbf{W}$ |
| $\mathrm{~T}_{\mathrm{J}}$ | Junction Temperature | $+\mathbf{2 0 0}$ | ${ }^{\circ} \mathrm{C}$ |
| $\mathrm{T}_{\text {STG }}$ | Storage Temperature | $\mathbf{- 6 5}$ to +150 | ${ }^{\circ} \mathrm{C}$ |

## Thermal Data

| $\mathrm{R}_{\mathrm{TH}(J-\mathrm{C})}$ | Junction-case Thermal Resistance | 15.0 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
| :---: | :--- | :---: | :---: |

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## ELECTRICAL SPECIFICATIONS [Tcase $=\mathbf{2 5}{ }^{\circ} \mathrm{C}$ ]

## STATIC

| Symbol | Test Conditions |  | Value |  |  | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  |  | Min. | Typ. | Max. |  |
| $\mathrm{BV}_{\text {cBo }}$ | $\mathrm{I}_{\mathrm{C}}=0.5 \mathrm{~mA}$ |  | 65 | --- | --- | V |
| $\mathrm{BV}_{\text {EBO }}$ | $\mathrm{I}_{\mathrm{E}}=0.1 \mathrm{~mA}$ |  | 4 | --- | --- | V |
| $\mathrm{BV}_{\text {cEo }}$ | $\mathrm{I}_{\mathrm{C}}=200 \mathrm{~mA}$ |  | 40 | --- | --- | V |
| $\mathrm{I}_{\text {ceo }}$ | $\mathrm{V}_{\text {CE }}=30 \mathrm{~V}$ |  | --- | --- | 0.1 | mA |
| $\mathrm{h}_{\text {FE }}$ | $\mathrm{V}_{\text {CE }}=5 \mathrm{~V}$ | $\mathrm{I}_{\mathrm{C}}=250 \mathrm{~mA}$ | 10 | --- | --- | --- |

## DYNAMIC

| Symbol | Test Conditions |  |  | Value |  |  |  |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  |  |  | Min. | Typ. | Max. | Unit |
| Pout | $\mathrm{f}=400 \mathrm{MHz}$ | $\mathrm{P}_{\text {IN }}=1 \mathrm{~W}$ | $\mathrm{V}_{\mathrm{cc}}=28 \mathrm{~V}$ | 3 | --- | --- | W |
| $\eta_{c}$ | $\mathrm{f}=400 \mathrm{MHz}$ | $\mathrm{P}_{\text {IN }}=1 \mathrm{~W}$ | $\mathrm{V}_{\mathrm{cc}}=28 \mathrm{~V}$ | 40 | --- | --- | \% |
| $\mathrm{G}_{\mathrm{P}}$ | $\mathrm{f}=400 \mathrm{MHz}$ | $\mathrm{P}_{\text {IN }}=1 \mathrm{~W}$ | $\mathrm{V}_{\mathrm{cc}}=28 \mathrm{~V}$ | 4.8 | --- | --- | dB |
| $\mathrm{C}_{\text {OB }}$ | $\mathrm{f}=1 \mathrm{MHz}$ | $\mathrm{V}_{\mathrm{CB}}=30 \mathrm{~V}$ |  | --- | --- | 10 | pF |

## PACKAGE MEGHANICAL DATA

## PABKAEE STYGEMTS7



|  | MINIMUM <br> INCHES/MM | MAXIMUM <br> INCHES/MM |  | MINIMUM <br> INCHES/MM | MAXIMUM <br> INCHES/MM |
| :---: | :---: | :---: | :---: | :---: | :---: |
| A | $.090 / 2,29$ | $.110 / 2,79$ | I | $.420 / 10,67$ | $.455 / 11,56$ |
| B | $.185 / 4,70$ | $.215 / 5,46$ | $\mid$ | $.140 / 3,56$ | $.160 / 4,06$ |
| C | $.420 / 10,67$ | $.440 / 11,18$ |  |  |  |
| D | $.030 / 0,76$ | $.046 / 1,17$ |  |  |  |
| E | $.320 / 8,13$ | $.360 / 9,14$ |  |  |  |
| F | $.090 / 2,29$ | $.135 / 3,43$ |  |  |  |
| G | $.215 / 5,46$ | $.320 / 8,13$ |  |  |  |
| H |  | $.480 / 12,19$ |  |  |  |

STANDARD STUD
SHORT STUD

